

Time-over-threshold method based on the time properties of plastic scintillators equipped with silicon photomultipliers for the BM@N High-Granular Neutron detector

Nikolay Karpushkin
INR RAS



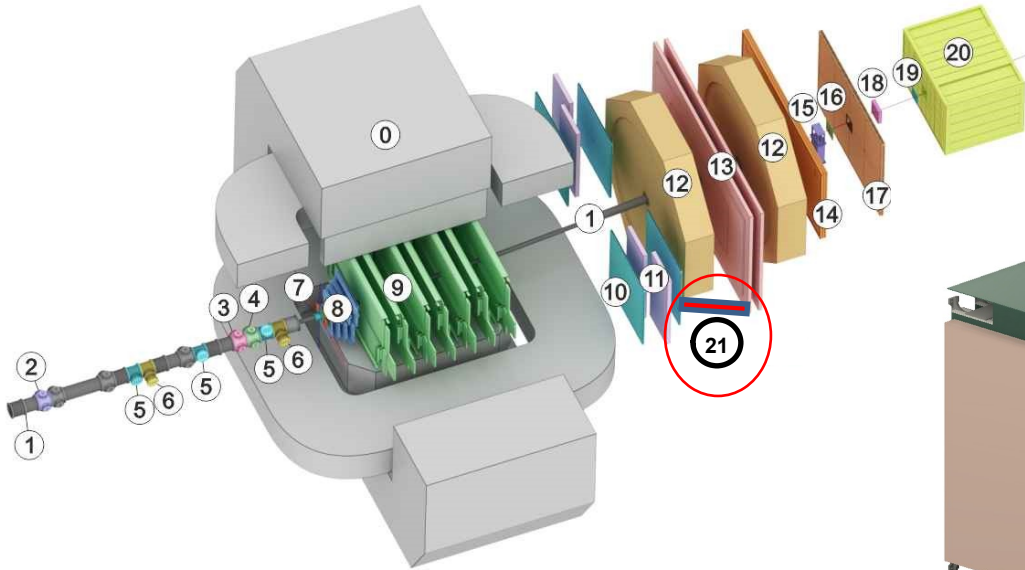
The work is supported by RSF grant No. 22-12-00132



The XXVth International Baldin Seminar on High Energy Physics Problems
"Relativistic Nuclear Physics and Quantum Chromodynamics"
BLTP JINR 22.09.2023

New High-Granular Neutron detector of the BM@N experiment

BM@N setup

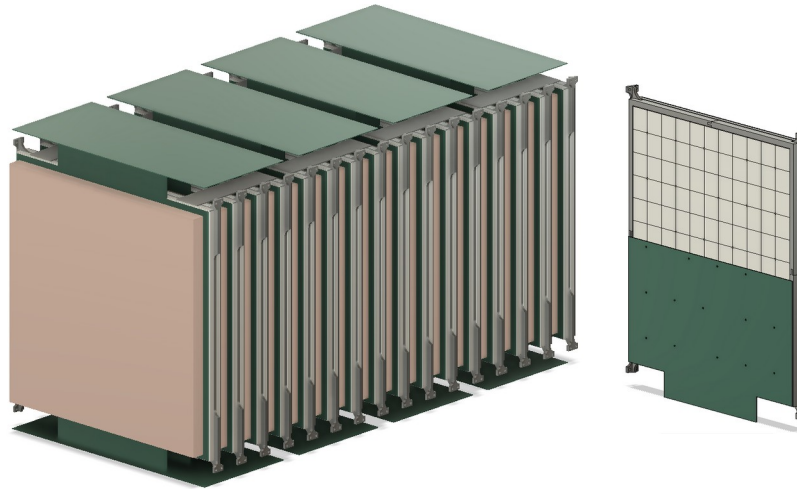
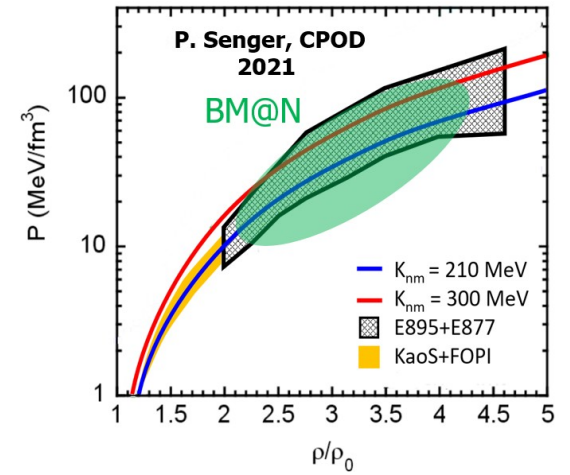


- | | |
|-------------------------------|---------------------------------|
| ■ Magnet SP-41 (0) | ■ TOF 700 (13) |
| ■ Vacuum Beam Pipe (1) | ■ ScWall (14) |
| ■ BC1, VC, BC2 (2-4) | ■ FD (15) |
| ■ SiBT, SiProf (5, 6) | ■ Small GEM (16) |
| ■ Triggers: BD + SiMD (7) | ■ CSC 2x1.5 m ² (17) |
| ■ FSD, GEM (8, 9) | ■ Beam Profilometer (18) |
| ■ CSC 1x1 m ² (10) | ■ FQH (19) |
| ■ TOF 400 (11) | ■ FHCAL (20) |
| ■ DCH (12) | ■ HGN (21) |

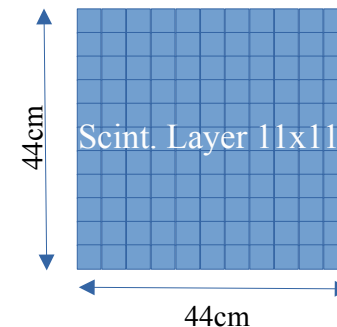
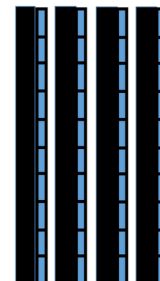
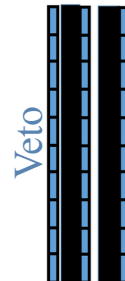
Goal: understanding the symmetry energy term of the EoS of strongly interacting matter in the uncovered energy region $(2-4) \rho_0$

How: by calculating anisotropic neutron flow and extracting $v_{1,2}^n / v_{1,2}^ch$

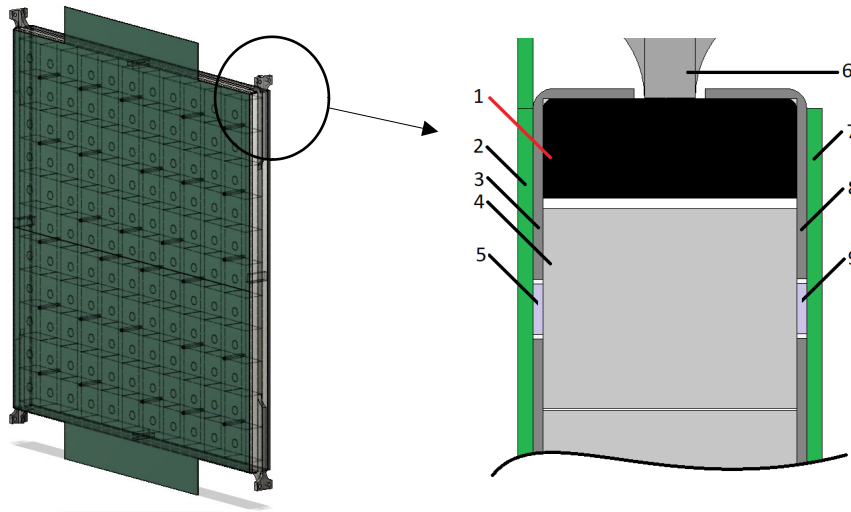
Measure: kinetic energy of neutrons by ToF



15 layers (Cu/Scint)



- Transverse size: 44 x 44 cm²
- number of layers: 15 + Veto
- total length of the HGN: ~ 95 cm (~3 λ_{in})
- structure of layer:
 - 3 cm Cu (absorber) + 2.5cm Scint. + 0.5cm (SiPM+FEE)
 - size of scintillation detectors (cells): 4x4x2.5 cm³
 - total number of cells: 1936
 - light readout: one SiPM 6x6 mm² per cell



- 1 – the frame of layer case
- 2 – two PCBs with 55 and 66 SiPMs**
- 3 and 8 - aluminum plates for both sides of the frame case with cutouts for SiPMs and LEDs
- 4 – scintillator**
- 5 – SiPM**
- 6 – layer support bracket
- 7 – LED PCB
- 9 – LED**

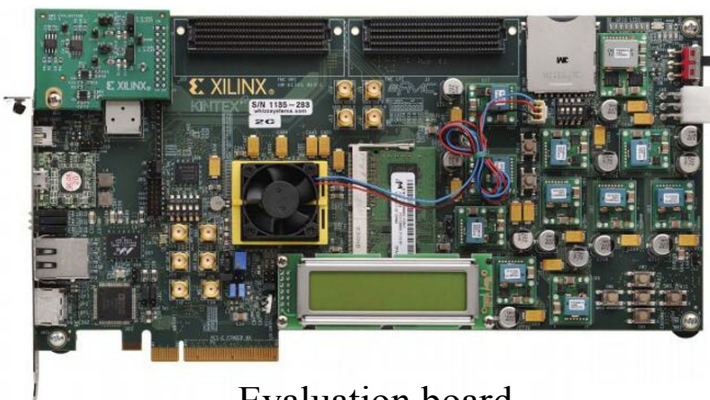
Readout scheme

1. Plastic scintillator light flash
2. SiPM EQR15 11-6060D-S
3. High-speed comparator with differential LVDS output
4. FPGA-based TDC (100 ps bin width)

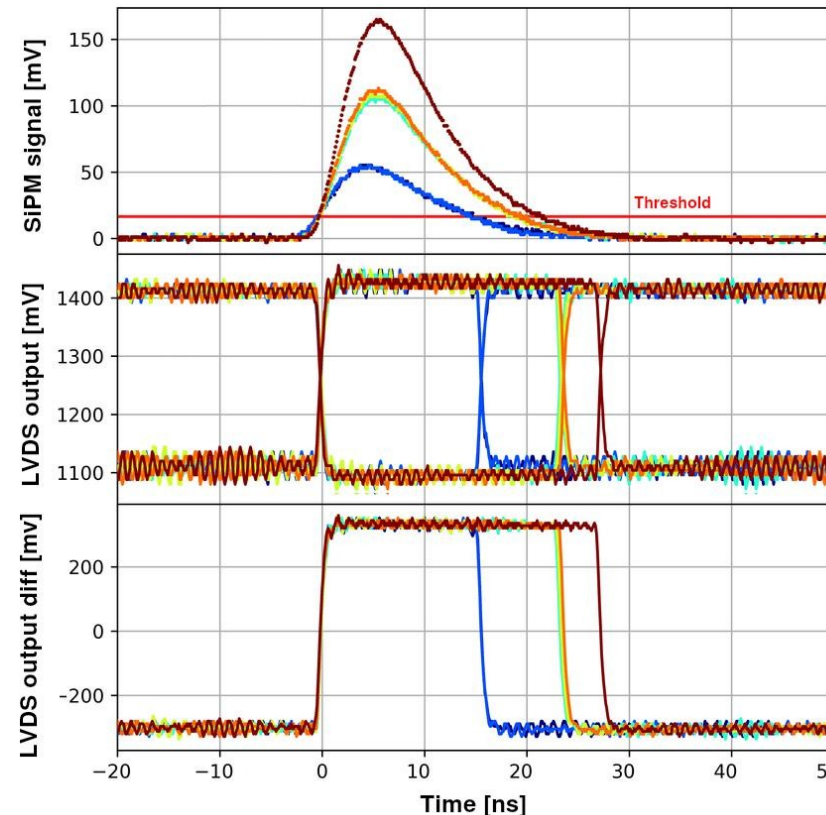
$$= \text{Response time} + T_{\text{OT}}$$

SiPM: NDL EQR15 11-6060D-S

- Active area $6 \times 6 \text{ mm}^2$
- Pixel size $15 \times 15 \text{ } \mu\text{m}^2$
- Total pixels: 160 000
- PDE: 45%
- Gain: 4×10^5



Evaluation board
Xilinx Kintex 7



Why do we need analytical description of signals?

- Need to correct for time-amplitude dependence
- Need the ability to calibrate readout channels with LED and recalculate calibration parameters to apply to scintillator signals

Analytical description of light signals captured by SiPM: main behavior

$$N_{ph}(t) = N_{ph}^0 e^{-t/\tau_{in}}$$

N_{ph}^0 – initial number of photons, τ_{in} – light decay constant.

Solution 1 – Process as convolution of photoelectron current $f(t)$ with SiPM impulse response function $g(t)$

$$f(t) = I_{p.e.} = \eta e \frac{dN_{ph}}{dt} \quad g(t) = \frac{1}{R_s C_T} e^{-t/R_s C_T}$$

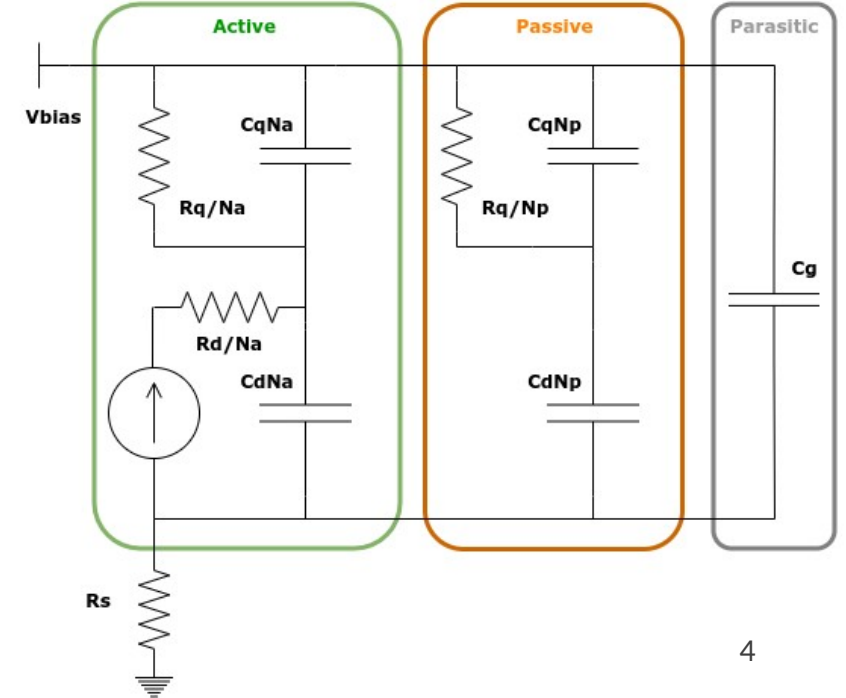
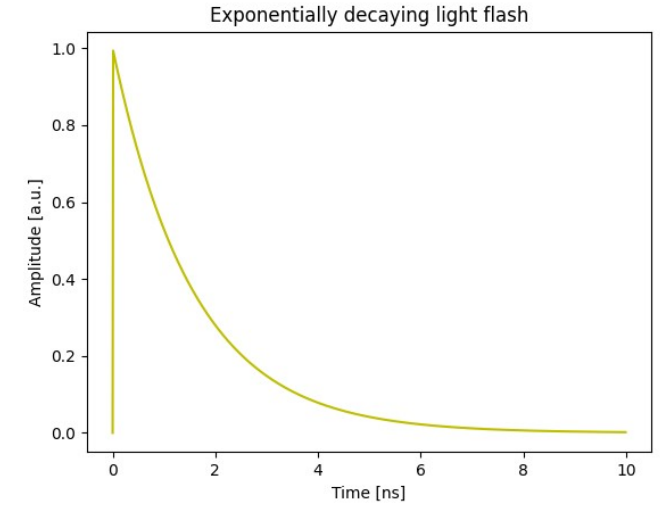
η – PDE, e – electron charge, R_s – load resistance + low intrinsic SiPM resistance, C_T – total SiPM capacitance.

$$V(t) = R_s (f * g)(t) = -\frac{\eta e N_{ph}^0}{C_T \tau_{in}} \int_0^t e^{-\frac{x}{\tau_{in}}} e^{-\frac{t-x}{R_s C_T}} dx = \frac{\eta e N_{ph}^0 R_s}{R_s C_T - \tau_{in}} \left(e^{-t/R_s C_T} - e^{-t/\tau_{in}} \right). \quad (1)$$

Solution 2 – Process as differential equation

$$\frac{dq}{dt} = I_{p.e.} + I_{recharge} \quad V_{bias} - R_s I_{recharge} = \frac{q}{C_T} \quad q(0) = C_T V_{bias}$$

$$V(t) = R_s I_{recharge} = \frac{\eta e N_{ph}^0 R_s}{R_s C_T - \tau_{in}} \left(e^{-t/R_s C_T} - e^{-t/\tau_{in}} \right). \quad (2)$$



Analytical description of light signals captured by SiPM: addressing derivative discontinuity

- Phase shift to the fast exponent by a value

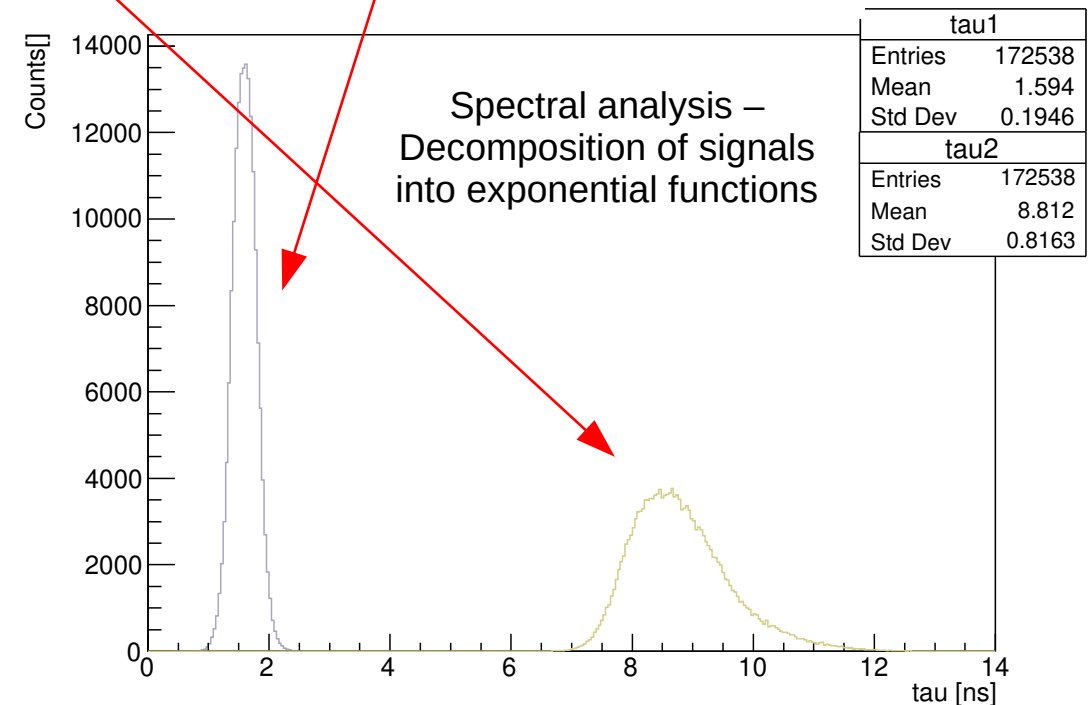
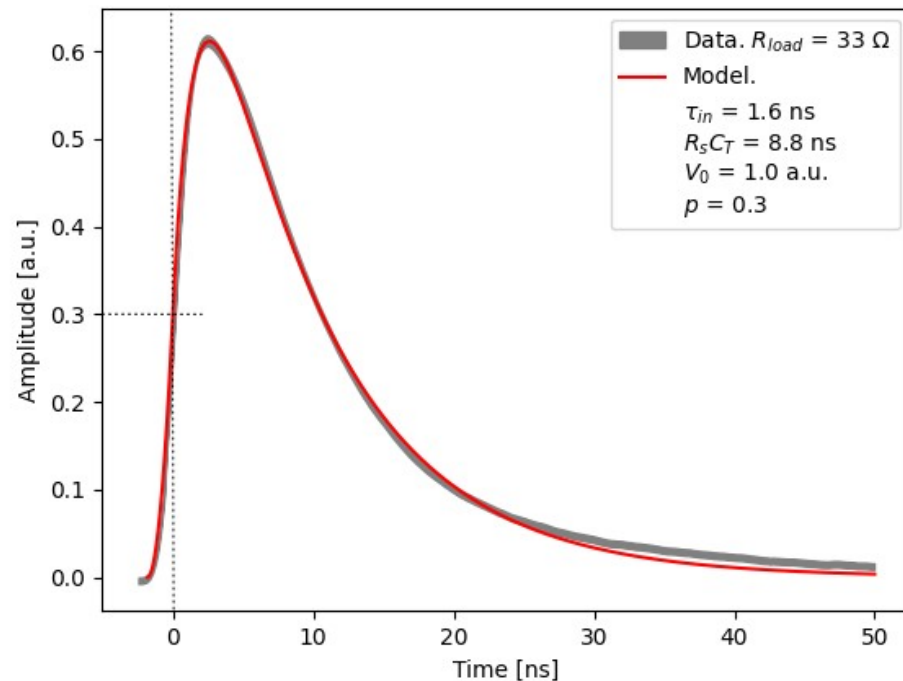
$$\tau_{in} \ln(1 - p)$$

- Match conditions with parabolic solution at time 0

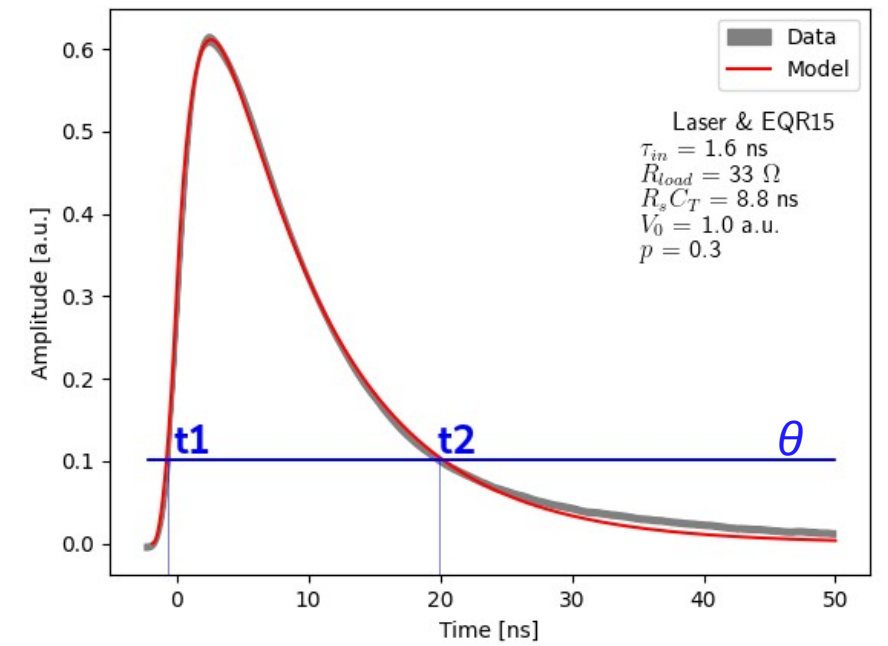
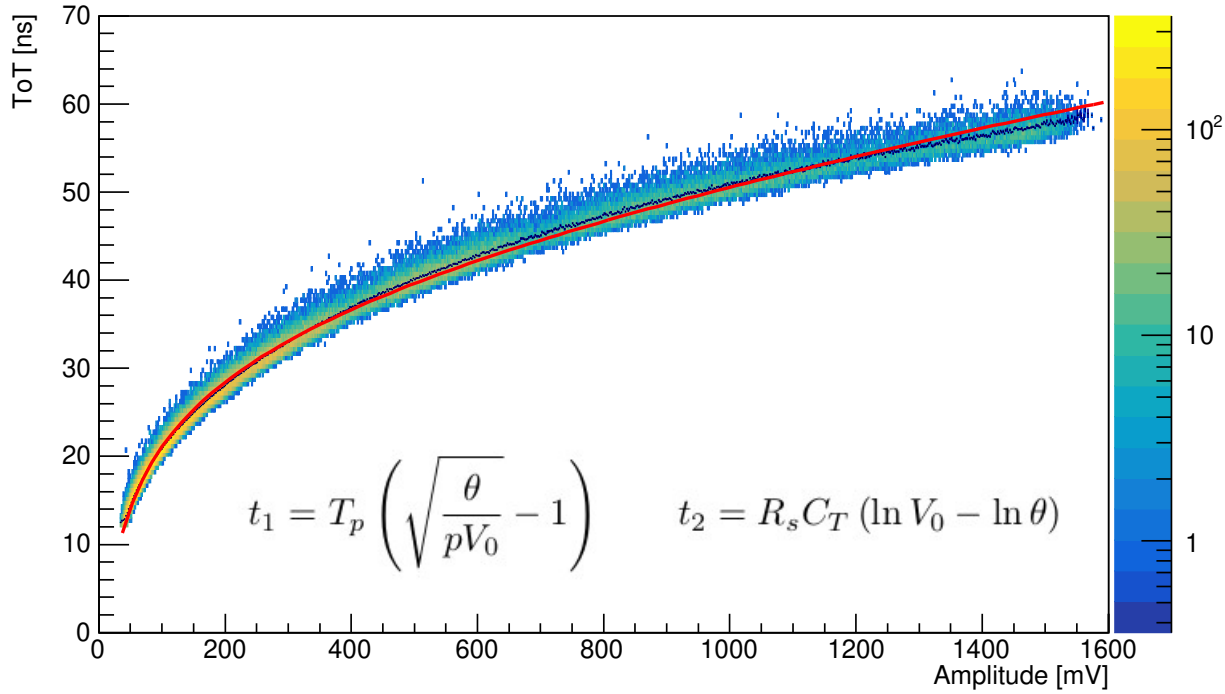
$$V_0 = \frac{\eta e N_{ph}^0 R_s}{R_s C_T - \tau_{in}} \quad T_p = \frac{2p\tau_{in} R_s C_T}{(1 - p)R_s C_T - \tau_{in}}$$

- Final form of analytic description

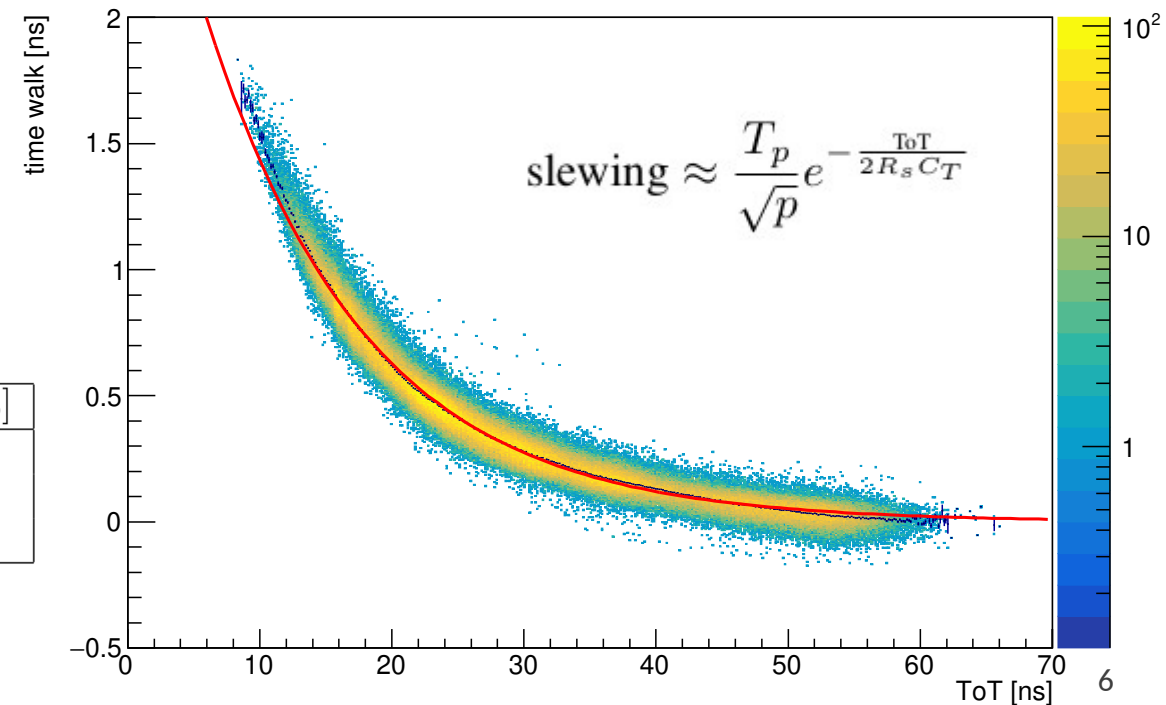
$$V(t) = \begin{cases} pV_0 \left(\frac{t}{T_p} + 1 \right)^2 & \text{if } -T_p < t < 0 \\ V_0 \left(e^{-\frac{t}{R_s C_T}} - (1 - p)e^{-\frac{t}{\tau_{in}}} \right) & \text{if } t \geq 0 \end{cases}$$



Analytical description of light signals captured by SiPM: parametrisation of slewing and ToT

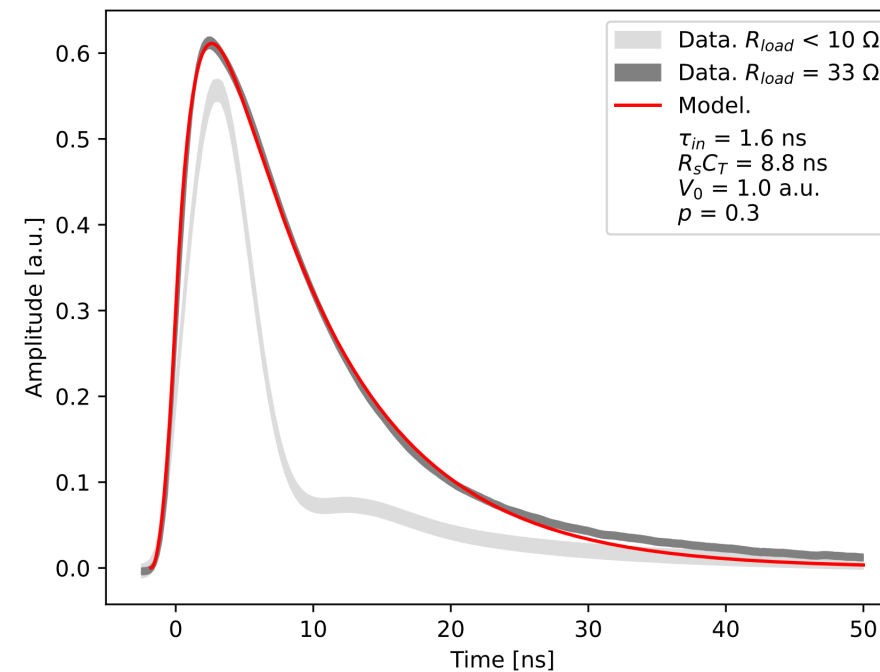


Light source	Decay time [ns]	Time res. w/o corr. [ps]	Time resolution [ps]
Laser	1.6 ± 0.2	88 ± 2	45 ± 0
EJ-230	2.8 ± 0.5	146 ± 2	74 ± 1
JINR	3.9 ± 0.7	261 ± 2	117 ± 1



Conclusion and next steps

- The analytical description of ToT is based on physical principles - parameters of light sources and SiPM response.
- The electronics are tuned so as not to distort the smooth physical behavior.
- Time resolution is significantly improved by applying slewing correction.
- It is possible to recalculate the calibration parameters taken from the LED for application to the light signals of a plastic scintillator (in the case of an undistorted SiPM impulse response).
- The method will be tested on larger amount of channels.



Thank you for your attention!

BACKUP